

FEATURES

- Double Side Cooling
- High Surge Capability
- High Mean Current
- Fatigue Free

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V_{DRM} V_{RRM} V	Conditions
DCR1675SZ52	5200	$T_{vj} = 0^\circ \text{ to } 125^\circ \text{C}$, $I_{DRM} = I_{RRM} = 500\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \text{ \& \ } V_{RSM} =$ $V_{DRM} \text{ \& \ } V_{RRM} + 100\text{V}$ respectively
DCR1675SZ51	5100	
DCR1675SZ50	5000	
DCR1675SZ49	4900	
DCR1675SZ48	4800	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1675SZ51

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	5200V
$I_{T(AV)}$	3770A
I_{TSM}	50000A
dV/dt^*	1000V/μs
dI/dt	300A/μs

*Higher dV/dt selections available

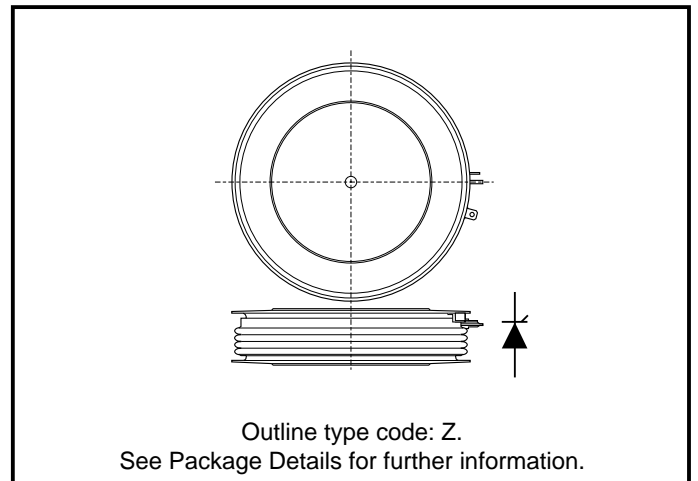


Fig. 1 Package outline

CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	3770	A
$I_{T(RMS)}$	RMS value	-	5920	A
I_T	Continuous (direct) on-state current	-	5486	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	2476	A
$I_{T(RMS)}$	RMS value	-	3889	A
I_T	Continuous (direct) on-state current	-	3333	A

CURRENT RATINGS

$T_{case} = 80^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	2975	A
$I_{T(RMS)}$	RMS value	-	4670	A
I_T	Continuous (direct) on-state current	-	4230	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	1920	A
$I_{T(RMS)}$	RMS value	-	3015	A
I_T	Continuous (direct) on-state current	-	2510	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}C$	50.0	kA
I^2t	I^2t for fusing	$V_R = 50\% V_{RRM}$ - 1/4 sine	12.5×10^6	A ² s
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}C$	62.5	kA
I^2t	I^2t for fusing	$V_R = 0$	19.5×10^6	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.0065	$^{\circ}C/W$
		Single side cooled	Anode dc	-	0.013	$^{\circ}C/W$
			Cathode dc	-	0.013	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 83.0kN with mounting compound	Double side	-	0.001	$^{\circ}C/W$
			Single side	-	0.002	$^{\circ}C/W$
T_{vj}	Virtual junction temperature	On-state (conducting)		-	135	$^{\circ}C$
		Reverse (blocking)		-	125	$^{\circ}C$
T_{stg}	Storage temperature range		-55	125	$^{\circ}C$	
-	Clamping force		74.0	91.0	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	500	mA	
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open circuit.	-	1000	V/ μs	
dI/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1000A Gate source 30V, 10 Ω $t_r = 0.5\mu s$ to 1A, $T_j = 125^{\circ}C$	Repetitive 50Hz	-	150	A/ μs
			Non-repetitive	-	300	A/ μs
$V_{T(TO)}$	Threshold voltage	At $T_{vj} = 125^{\circ}C$	-	1.0	V	
r_T	On-state slope resistance	At $T_{vj} = 125^{\circ}C$	-	0.15	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 20V, 10 Ω $t_r = 0.5\mu s$, $T_j = 25^{\circ}C$	-	1.1	μs	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$	-	650	mA	
I_H	Holding current	$T_j = 25^{\circ}C$, $R_{g-k} = \infty$	-	200	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.5	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	500	mA
V_{GD}	Gate non-trigger voltage	At V_{DRM} , $T_{case} = 125^{\circ}C$	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak reverse gate voltage		5	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	A
P_{GM}	Peak gate power	See table, gate characteristics curve	150	W
$P_{G(AV)}$	Mean gate power		10	W

CURVES

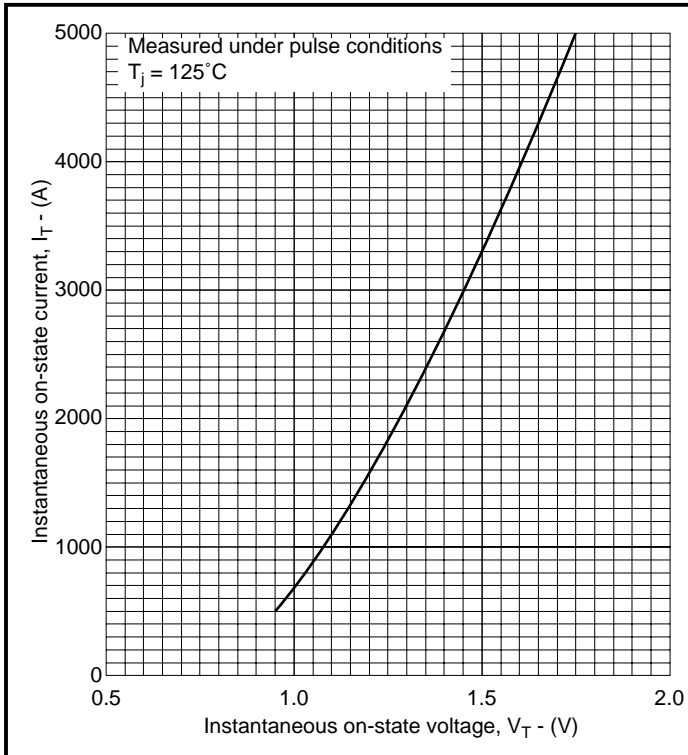


Fig.2 Maximum (limit) on-state characteristics

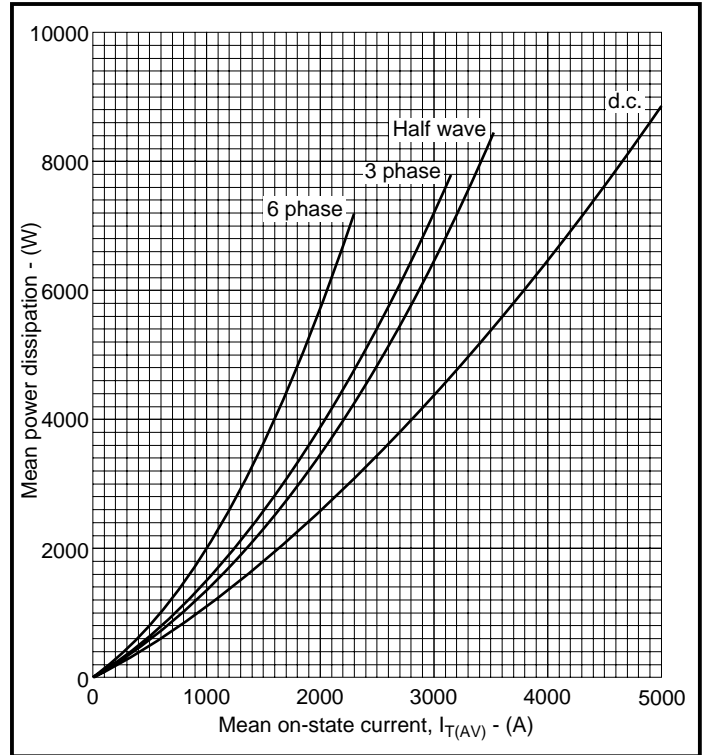


Fig.3 Dissipation curves

V_{TM} Equation:-

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where

$A = 0.8497627$

$B = -0.03614853$

$C = 5.286579 \times 10^{-5}$

$D = 0.01334724$

these values are valid for $T_j = 125^\circ\text{C}$ for I_T 500A to 5000A

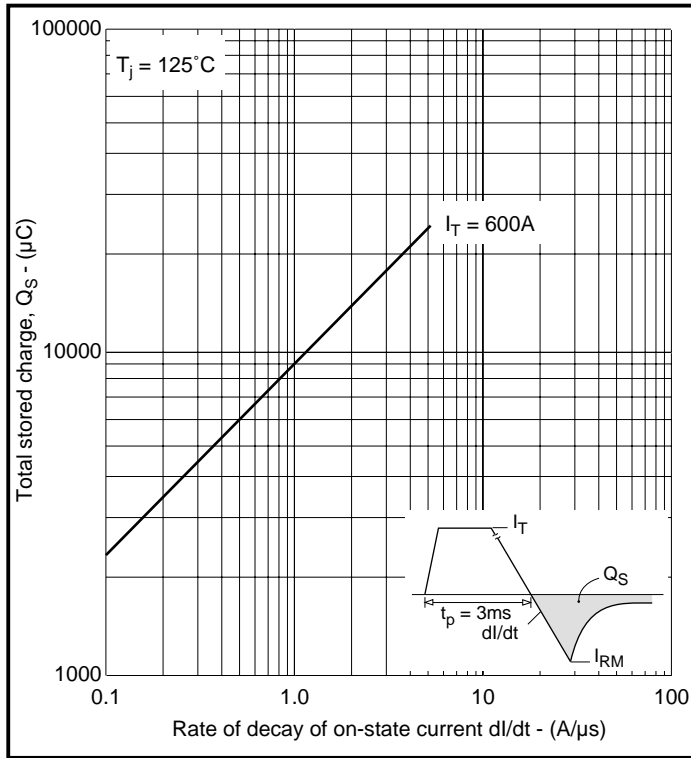


Fig.4 Stored charge

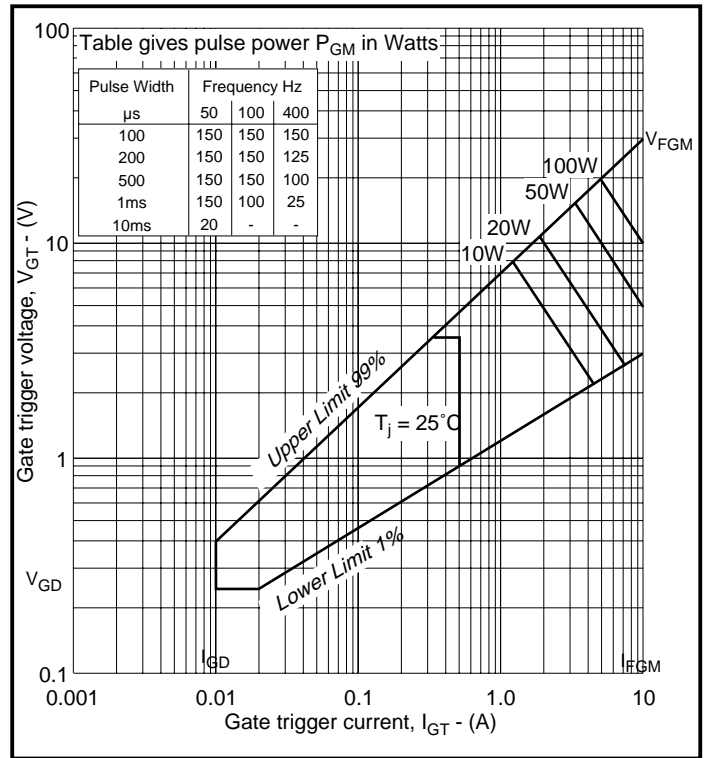


Fig.5 Gate characteristics

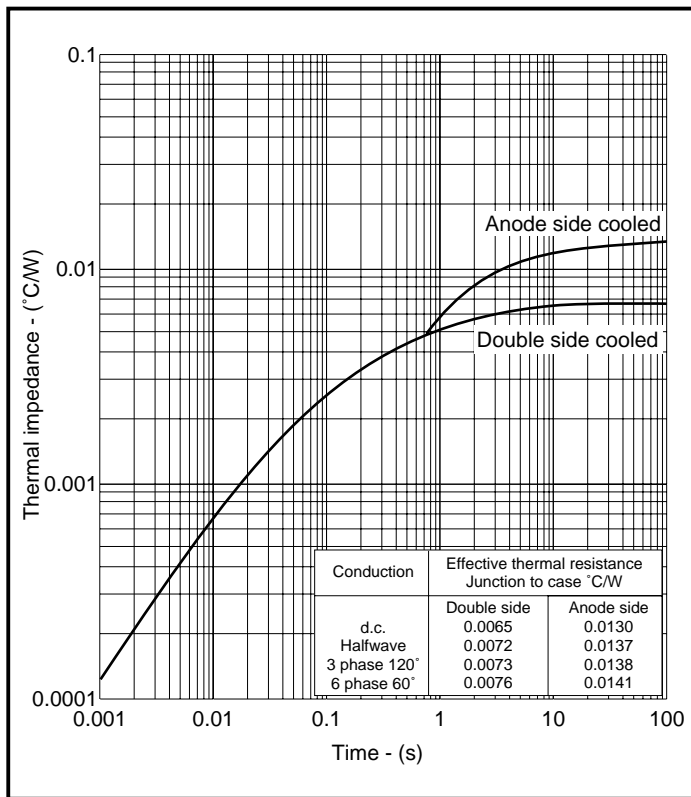


Fig.6 Transient thermal impedance - junction to case

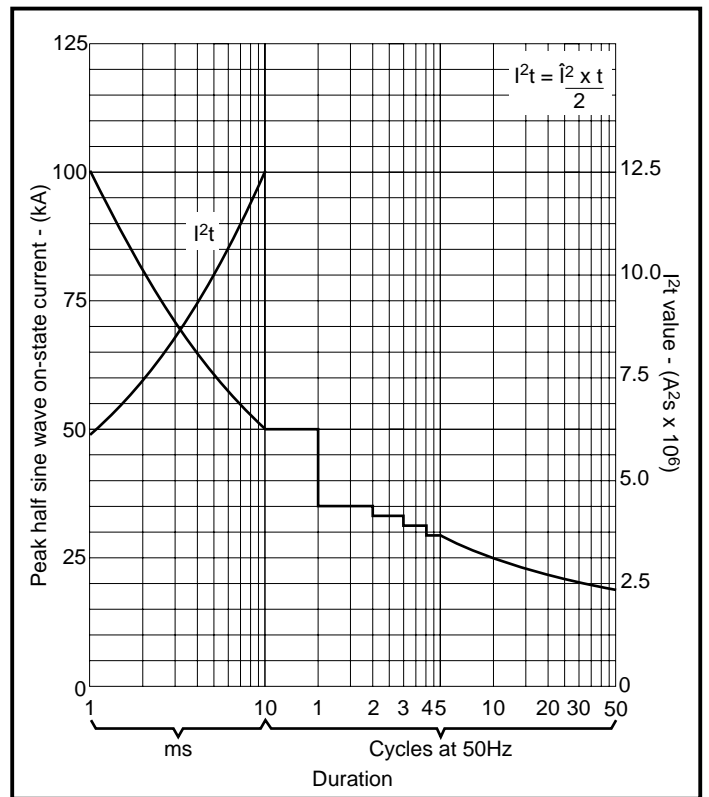
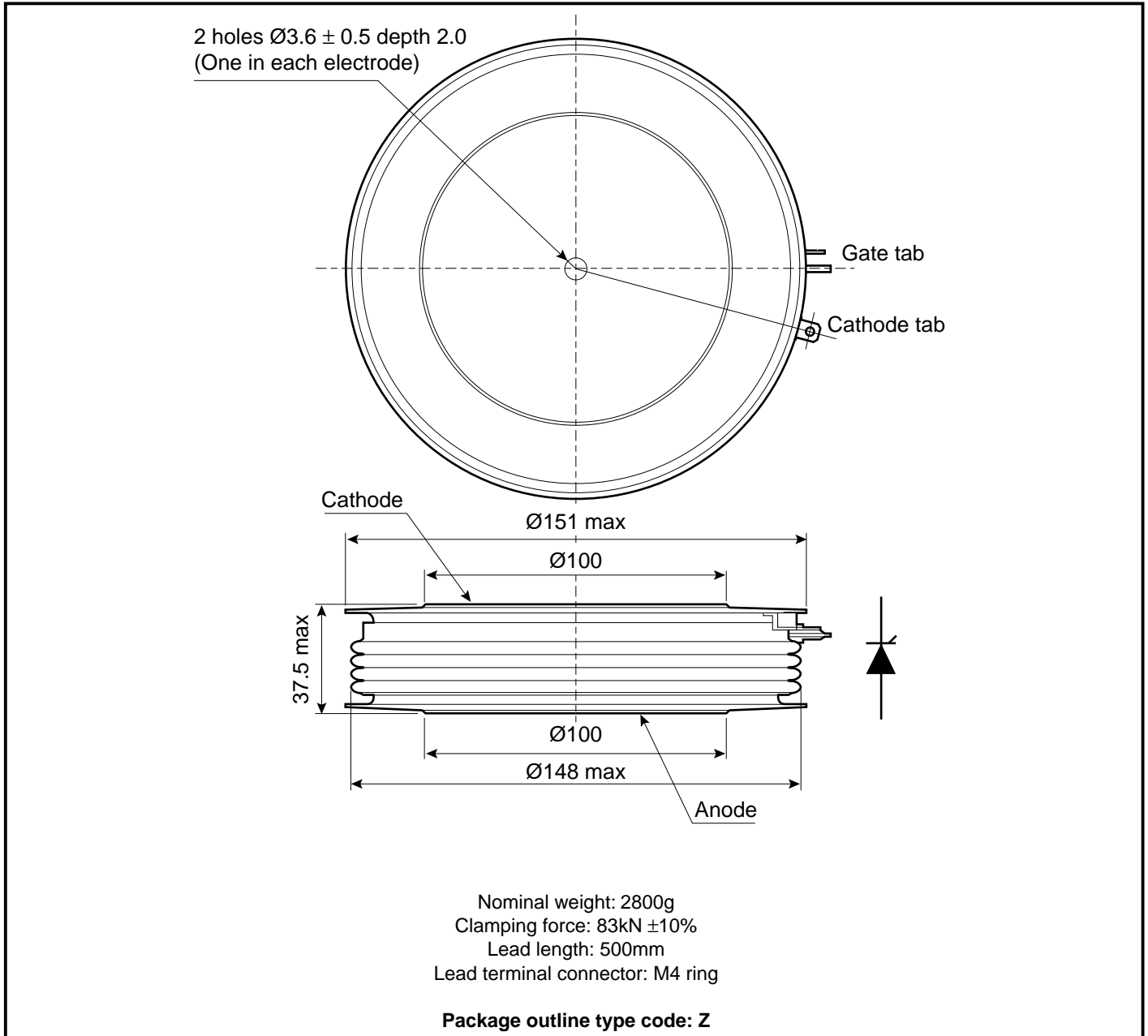


Fig.7 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} at $T_{case} = 125^\circ\text{C}$)

PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



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Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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